International Conference on Solid State & IC Technology To Be Held in Beijing

Plenary Sessions to Cover Opportunities and Joint Ventures in China

The Second International Conference on Solid State and Integrated Circuit Technology wil be held October 22-28, 1989 in Beijing, China. The conference is being sponsored by the University of California at Berkeley, Continuing Education in Engineering, University Extension, and by the Chinese Institute of Electronics. The technical focus will be a broad review of materials and processing issues associated with the fabrication of semiconductor and IC devices.

The seven-day conference will offer four days of talks and panel discussions and feature four technical symposia: Amorphous Silicon, Superconductor Electronic Materials and Applications, Computer-Aided Design, and Optoelectronic Materials.

The Beijing location will provide an important opportunity to establish contacts with a large number of Chinese scientists and technologists. Several plenary sessions will be devoted to opportunities and joint ventures in China. Tours of factories, research institutes, universities, and other sites in the Beijing area will emphasize computer, communication, and IC fabrication facilities. Opportunities for additional interaction will be provided at the factory sites and research laboratories.

Abstracts Due January 9, 1989

Papers are solicited on:

- Silicon Technology, Materials and Processing—device physics and performance; novel device structures; bipolar and MOS devices; yield and reliability; failure mechanisms; circuit design, integration and networking; clean room technology and ultrapure processing; wafer processing, specifications and inspection; epitaxial growth (MBE, CVD, SPE, and SOI); ion implantation and mixing; dielectric materials and ultrathin gates; silicides, diffusion barriers, thin film reactions and interfaces; multilayer interconnections studs and planarization; selective deposition of metals; circuit miniaturization (lithography, resist and RIE); characterization and analysis techniques
- Compound Semiconductor Technology, Materials and Processing
- Computer-Aided Design
- Amorphous Silicon
- Superconductor Electronic Materials and Applications
- Optoelectronic Materials

Send abstracts to arrive by January 9, 1989 to: Linda Reid, Continuing Education in Engineering, University Extension, University of California, 2223 Fulton St., Berkeley, CA 94720, USA; fax (415) 642-8683. The conference language is English and the technical proceedings will be available at the conference.

Technical Program Information

For more information about the technical program contact either Michael Current, Applied Materials, 3050 Bowers Ave., MS 0709, Santa Clara, CA 95054, USA, telephone (408) 748-5750; or King-Ning Tu, IBM T.J. Watson Research Center, P.O. Box 218, Yorktown Heights, NY 10598, USA, telephone (914) 945-1802.

Registration

To register contact: Continuing Education in Engineering, University, Extension, University of California, 2223 Fulton St., Berkeley, CA 94720, telephone (415) 642-4151, fax (415) 643-8683, telex 9103667114 UC BERK BERK.

36th International Field Emission Symposium Slated for 1989

The 36th International Field Emission Symposium will be held at St. Catherine's College, Oxford, United Kingdom, July 31 to August 4, 1989. The themes of the meeting will be field emission and field ion microscopy, atom probe microanalysis, the production of focused electron and ion beams by field emission methods (including liquid metal ion sources), and the applications of these experimental tools in surface studies, materials science, microlithography, and nanotechnology. The proceedings will be published after refereeing as a special volume of *Journal de Physique*.

The meeting is being organized by the Royal Microscopical Society in collaboration with the International Field Emission Society. For information about the meeting and details about submitting papers, contact: The Administrator, Royal Microscopical Society, 37/38 St. Clements, Oxford OX4 1AJ, U.K.; telephone 865-248768. □